

IDS - 07/13/2006

Substitute for form 1449A/PTO				<b>Complete If Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				Application Number	10/660,048
				Filing Date	September 11, 2003
				First Named Inventor	Lanzerotti, et al.
				Group Art Unit	2826
				Examiner Name	Quach, Tuan N.
Sheet	1	of	1	Attorney Docket Number	BUR920010146US2

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant/Inventor of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
TQ		5,734,183		Morishita	03/31/1998	
TQ		6,246,104 B1		Tsuda, et al.	06/12/2001	

  

U.S. PATENT PUBLICATIONS						
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant/Inventor of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
TQ		2002/0192918 A1		Takagi, et al.	12/19/2002	
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FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Number			Name of Patentee or Applicant/Inventor of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number	Kind Code <sup>5</sup> (if known)				

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>

Examiner Signature	/Tuan Quach/	Date Considered	08/19/06
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<sup>1</sup> Unique citation designation number. <sup>2</sup> See attached Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				ATTY DOCKET NO. <b>BUR920010146US2</b>		SERIAL NO. 10/660,048 Not Yet Assigned	
				Lanzerotti et al.			
				FILING Concurrently Herewith		GROUP Unknown	
<b>U.S. PATENT DOCUMENTS</b>							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
TQ		4,885,614	12/05/1989	Furukawa et al.	_____	_____	
		5,116,455	05/26/1992	Daly	_____	_____	
		5,321,302	06/14/1994	Shimawaki	_____	_____	
		5,338,945	08/16/1994	Baliga et al.	_____	_____	
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		5,404,028	04/04/1995	Metzger et al.	_____	_____	
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		5,783,845	07/21/1998	Kondo et al.	_____	_____	
TQ		5,986,287	11/16/1999	Eberl et al.	_____	_____	
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
TQ		JP11312685A	11/09/1999	Japan w/Abstract	_____	_____	<input type="checkbox"/> <input checked="" type="checkbox"/>
		JP2000012558A	01/14/2000	Japan w/Abstract	_____	_____	<input type="checkbox"/> <input checked="" type="checkbox"/>
		JP92000174033A	06/23/2000	Japan w/Abstract	_____	_____	<input type="checkbox"/> <input checked="" type="checkbox"/>
TQ		WO 98/26457	06/18/1998	Germany	_____	_____	<input type="checkbox"/> <input checked="" type="checkbox"/>
<b>OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)</b>							
TQ		Lanzerotti et al., "Suppression of Boron Outdiffusion in SiGe HBTs by Carbon Incorporation", 1996 IEEE, pp. 10.2.1 - 10.2.4					
TQ		Stock et al. "Carbon Incorporation in Silicon for Suppressing Interstitial-Enhanced Boron Diffusion", Applied Physics Letter, March 13, 1995, Vol. 66, Issue 11, pp. 1370-1372					
EXAMINER  /Tuan Quach/				DATE CONSIDERED  08/21/2006			
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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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		6,096,617	08/01/2000	Kizuki	_____	_____	
		6,107,151	08/22/2000	Enquist	_____	_____	
		6,229,197	05/08/2001	Plumton et al.	_____	_____	
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		5,814,843	09/1998	Ohkubo, Michio	_____	_____	
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<b>FOREIGN PATENT DOCUMENTS</b>							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES    NO
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
TQ		Ghanti et al., "Control of Implant-Damage-Enhanced Boron Diffusion in Epitaxially Grown Si/p-Siz-x Gex/n-Si Heterojunction Bipolar Transistors", Journal of Electronic Materials, Vol. 24, No. 8, 1995, pp. 999-1002					
TQ		Bodnar et al., "Growth of Ternary Alloy Siz-x-yGexCy By Rapid Thermal Chemical Vapor Deposition", Journal Vac. Science Technology, A., Vol. 1. 13, N. 5, Sept/Oct. 1995, pp.2336-2340					
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**Concurrently Herewith**

GROUP

**Unknown**

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

## **FOREIGN PATENT DOCUMENTS**

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

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TQ			Poate et al., "Ion Implantation and Transient Enhanced Diffusion", IEDM 95-77, IEEE 1995, pp. 4.1.1 - 4.1.4

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/Tuan Quach/

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